

IN THE CLAIMS

Please cancel claims 25 and 27-29 without prejudice.

The following are the only claims pending in the present application:

1-7. (Cancelled)

8. (Previously presented) A wafer comprising:

a layer of solid diamond;

a final monocrystalline semiconductor film on the layer of solid diamond;

and

a layer of monocrystalline semiconductor material directly on the final monocrystalline semiconductor film with a boundary defined between the final monocrystalline semiconductor film and the layer of monocrystalline semiconductor material for purposes of shearing the layer of monocrystalline semiconductor material from the final monocrystalline semiconductor film.

9. (Original) The wafer of claim 8 wherein the layer of solid diamond is at least 200 mm wide.

10. (Original) The wafer of claim 9 wherein the layer of monocrystalline semiconductor material is at least 200 mm wide.

11. (Original) The wafer of claim 10 wherein the layer of monocrystalline semiconductor material is a layer of monocrystalline silicon.
12. (Previously presented) A singulated die comprising:
- a layer of solid diamond having a thickness of less than 150 microns;
  - a layer of monocrystalline semiconductor material on the layer of solid diamond;
  - a bonding material bonding the layer of solid diamond to the layer of monocrystalline semiconductor material; and
  - an integrated circuit on a side of the layer of monocrystalline semiconductor material opposing the layer of solid diamond.
13. (Previously presented) The singulated die of claim 12 wherein the layer of solid diamond has an exposed lower surface.
14. (Original) The singulated die of claim 13 wherein the layer of monocrystalline semiconductor material is a layer of monocrystalline silicon.
15. (Previously presented) The singulated die of claim 14 further comprising:
- a layer of polysilicon between the layer of monocrystalline silicon and the layer of solid diamond.

16. (Original) The singulated die of claim 12 further comprising:  
a plurality of contacts on the integrated circuit.
17. (Previously presented) The singulated die of claim 12 wherein the die has a  
rectangular outline when viewed from above.
- 18-29. (Cancelled)